

### Features

- GaN on Si HEMT D-Mode Integrated Amplifier
- Suitable for Linear & Saturated Applications
- Broadband Operation from 20 - 2700 MHz
- 50  $\Omega$  Input Matched
- 28 V Operation
- 45% Drain Efficiency
- 100% RF Tested
- Lead-Free 4 mm 24-lead PQFN Package
- RoHS\* Compliant

### Applications

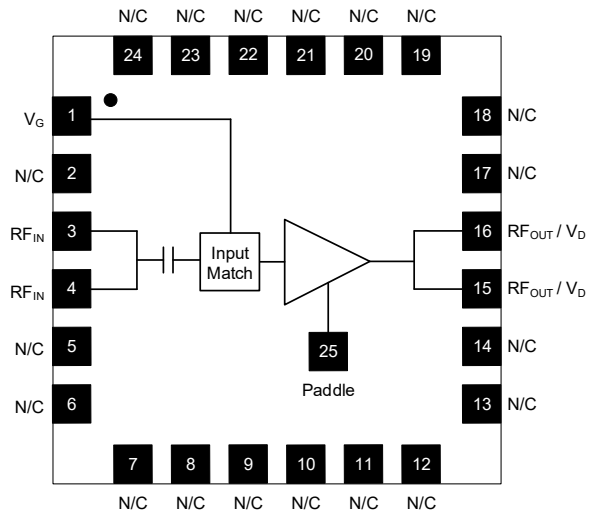
- Test & Measurement
- Defense Communications
- Land Mobile Radio
- Wireless Infrastructure

### Description

The NPA1008A is an integrated GaN on silicon power amplifier optimized for 20 - 2700 MHz operation. This amplifier has been designed for saturated and linear operation with output levels to 5 W (37 dBm) assembled in a lead-free 4 mm 24-lead QFN plastic package.

The NPA1008A is ideally suited for general purpose narrowband to broadband applications.

### Functional Schematic



### Pin Designations

Pin #	Pin Name	Function
1	$V_G$	Gate - DC Bias
2	N/C <sup>1</sup>	No Connection
3,4	$RF_{IN}$	RF Input
5-14	N/C <sup>1</sup>	No Connection
15,16	$RF_{OUT} / V_D$	RF Output / Drain
17-24	N/C <sup>1</sup>	No Connection
25	Paddle <sup>2</sup>	Ground / Source

1. All no connection pins may be left floating or grounded.
2. The exposed pad centered on the package bottom must be connected to RF and DC ground. This path must also provide a low thermal resistance heat path.

### Ordering Information

Part Number	Package
NPA1008A	Bulk Quantity
NPA1008A-TR0500	500 piece reel
NPA1008A-SMB	Sample Board

\* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

**RF Electrical Specifications:  $T_C = 25^\circ\text{C}$ ,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 88\text{ mA}$**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Small Signal Gain	CW, 1900 MHz	$G_{SS}$	-	15.6	-	dB
Gain	CW, $P_{OUT} = 37\text{ dBm}$ , 1900 MHz	$G_P$	10.5	12.0	-	dB
Saturated Output Power	CW, 1900 MHz	$P_{SAT}$	-	38.9	-	dBm
Drain Efficiency	CW, 1900 MHz	$\eta_{SAT}$	44	47.0	-	%
Power Added Efficiency	CW, $P_{OUT} = 37\text{ dBm}$ , 1900 MHz	PAE	-	44.7	-	%
Ruggedness	All phase angles	$\Psi$	VSWR = 15:1, No Device Damage			

**DC Electrical Specifications:  $T_C = 25^\circ\text{C}$**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 100\text{ V}$	$I_{DLK}$	-	4	-	mA
Gate-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GLK}$	-	2	-	mA
Gate Threshold Voltage	$V_{DS} = 28\text{ V}$ , $I_D = 4\text{ mA}$	$V_T$	-3.0	-2.0	-1.0	V
Gate Quiescent Voltage	$V_{DS} = 28\text{ V}$ , $I_D = 88\text{ mA}$	$V_{GSQ}$	-2.6	-1.7	-0.8	V
On Resistance	$V_{DS} = 2\text{ V}$ , $I_D = 45\text{ mA}$	$R_{ON}$	-	1.2	-	$\Omega$
Saturated Drain Current	$V_{DS} = 7\text{ V}$ pulsed, pulse width 300 $\mu\text{s}$	$I_{D(SAT)}$	-	2.3	-	A

**Absolute Maximum Ratings**<sup>3,4,5,6,7</sup>

Parameter	Absolute Maximum
Drain Source Voltage, $V_{DS}$	100 V
Gate Source Voltage, $V_{GS}$	-10 to 3 V
Gate Current, $I_G$	12 mA
Storage Temperature Range	-65°C to +150°C
Case Operating Temperature Range	-40°C to +85°C
Channel Operating Temperature Range, $T_{CH}$	-40°C to +225°C
Absolute Maximum Channel Temperature	+250°C

3. Exceeding any one or combination of these limits may cause permanent damage to this device.
4. MACOM does not recommend sustained operation near these survivability limits.
5. Operating at drain source voltage  $V_{DS} < 32$  V will ensure  $MTTF > 1 \times 10^7$  hours.
6. Operating at nominal conditions with  $T_{CH} \leq 225^\circ\text{C}$  will ensure  $MTTF > 1 \times 10^7$  hours.
7.  $MTTF$  may be estimated by the expression  $MTTF$  (hours) =  $A e^{[B + C/(T+273)]}$  where T is the channel temperature in degrees Celsius, A = 3.686, B = -35.00, and C = 25.416.

**Thermal Characteristics**<sup>8,9</sup>

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance	$V_{DS} = 28$ V, $T_J = 200^\circ\text{C}$	$\Theta_{JC}$	12.1	°C/W

8. Junction temperature ( $T_J$ ) measured using IR Microscopy. Case temperature measured using thermocouple embedded in heat-sink.
9. The thermal resistance of the mounting configuration must be added to the device  $\Theta_{JC}$ , for proper  $T_J$  calculation during operation. The recommended via pattern, shown on page 4, on a 20 mil thick, 1 oz plated copper, PCB adds an additional 4 °C/W to the typical value.

**Handling Procedures**

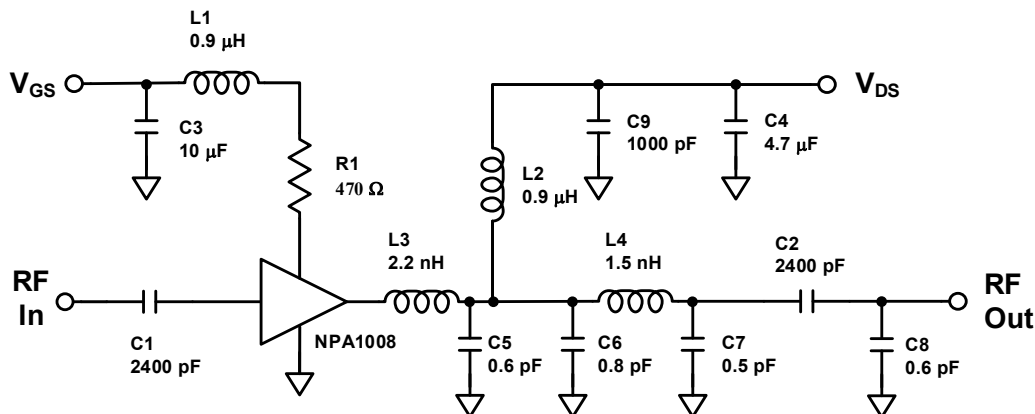
Please observe the following precautions to avoid damage:

**Static Sensitivity**

Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1B devices.

## Evaluation Board and Recommended Tuning Solution

### 20 - 2700 MHz Broadband Circuit



### Description

Parts measured on evaluation board (20-mil thick RO4350). The PCB's electrical and thermal ground is provided using a standard-plated densely packed via hole array (see recommended via pattern).

Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

### Bias Sequencing

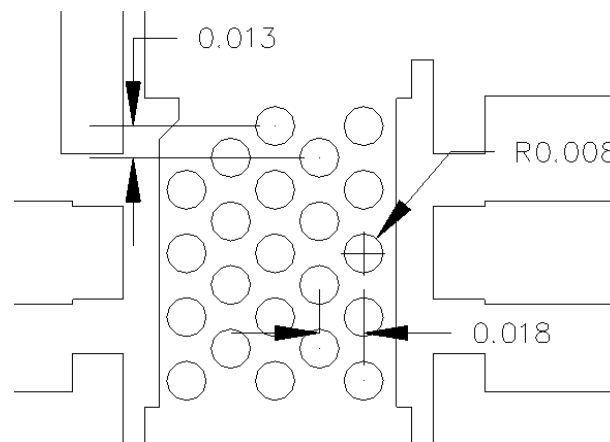
#### Turning the device ON

1. Set  $V_{GS}$  to the pinch-off ( $V_P$ ), typically -5 V.
2. Turn on  $V_{DS}$  to nominal voltage (28 V).
3. Increase  $V_{GS}$  until the  $I_{DS}$  current is reached.
4. Apply RF power to desired level.

#### Turning the device OFF

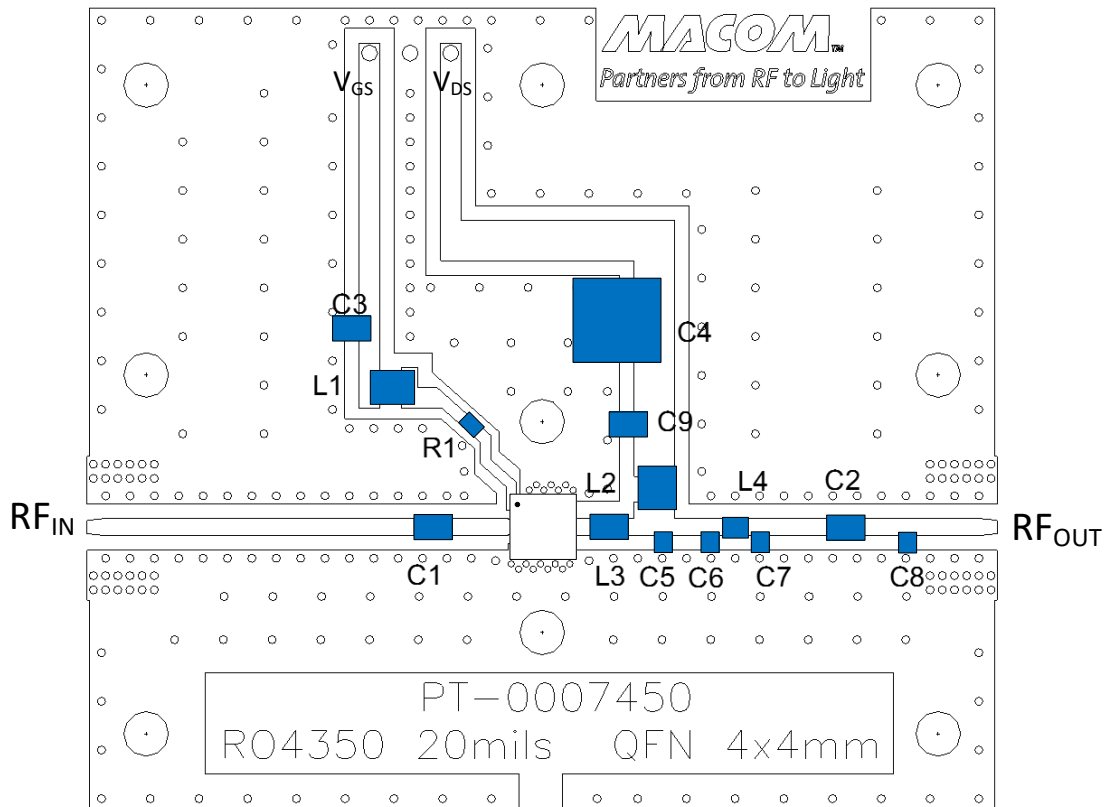
1. Turn the RF power off.
2. Decrease  $V_{GS}$  down to  $V_P$ .
3. Decrease  $V_{DS}$  down to 0 V.
4. Turn off  $V_{GS}$ .

### Recommended Via Pattern (All dimensions shown as inches)



**Evaluation Board and Recommended Tuning Solution**

**20 - 2700 MHz Broadband Circuit**

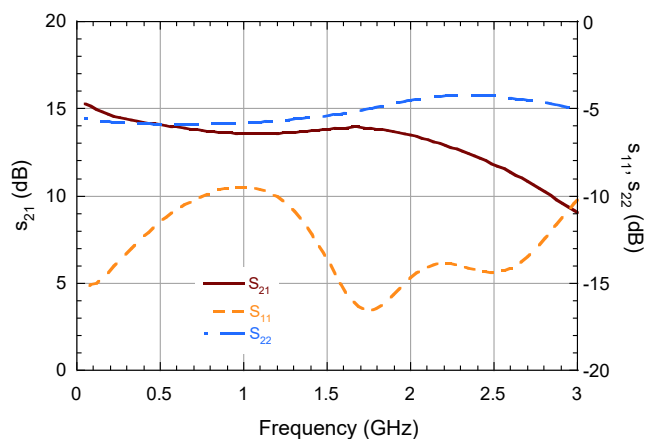


**Parts list**

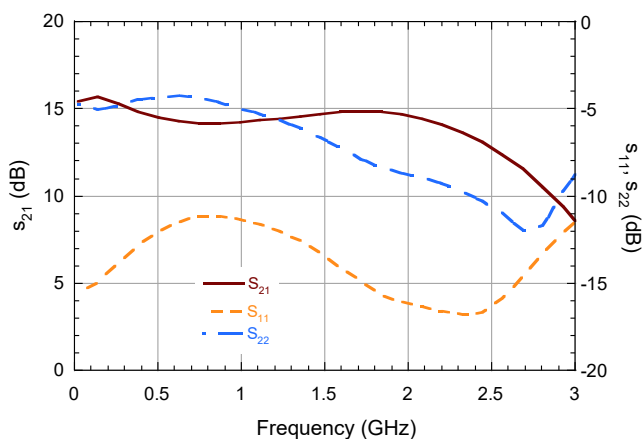
Reference	Value	Tolerance	Manufacturer	Part Number
C1, C2	2400 pF	-	Dielectric Labs, Inc.	C08BL242X-5UN-X0
C3	10 $\mu$ F	10%	TDK	C2012XR1C106M085AC
C4	4.7 $\mu$ F	10%	TDK	C5750X7R2A475K230KA
C5, C8	0.6 pF	0.1 pF	ATC	800A0R6BT250X
C6	0.8 pF	0.1 pF	ATC	800A0R8BT250X
C7	0.5 pF	0.1 pF	ATC	800A0R5BT250X
C9	1000 pF	10%	Kemet	C0805C102K1RACTU
R1	470 $\Omega$	10%	Panasonic	ERJ-P03F4700V
L1, L2	0.9 $\mu$ H	10%	Coilcraft	1008AF-901XJLC
L3	2.2 nH	$\pm 0.2$ nH	AVX	L08052R2CEW
L4	1.5 nH	$\pm 0.2$ nH	AVX	L06031R5CGS
PCB	Rogers RO4350, $\epsilon_r=3.5$ , 0.020"			

**Typical Performance as measured in the Broadband Evaluation Board:  
CW,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 88\text{ mA}$ ,  $T_C = 25^\circ\text{C}$  (unless noted)**

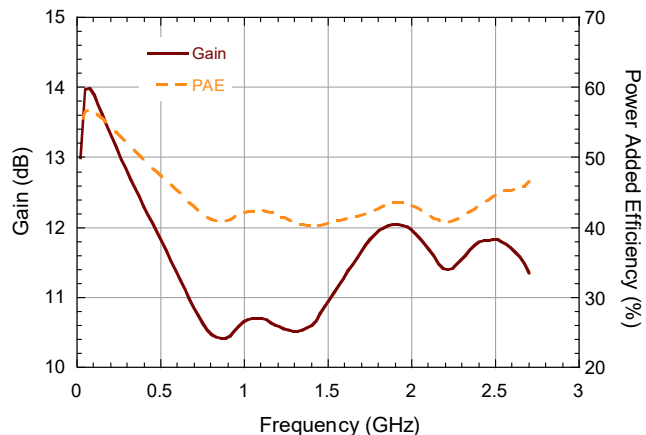
**Device s-parameters (Deembedded)**



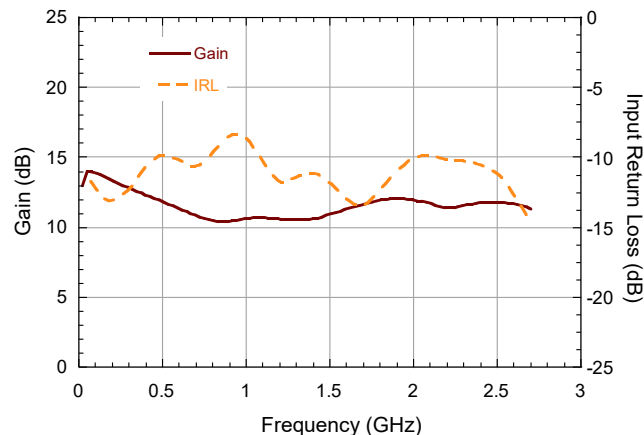
**Broadband Circuit s-Parameters**



**Performance vs. Frequency at  $P_{OUT} = 37\text{ dBm}$**

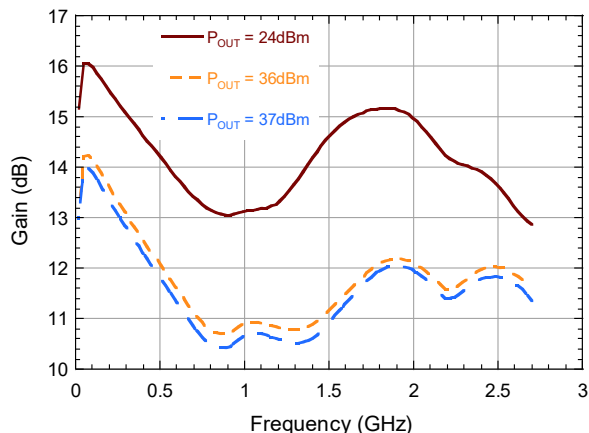


**Performance vs. Input Return Loss at  $P_{OUT} = 37\text{ dBm}$**

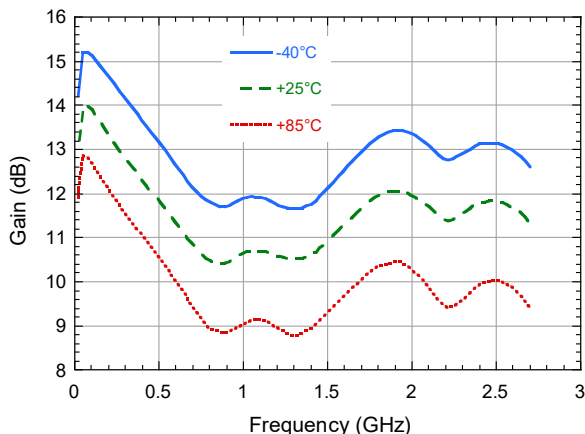


Typical Performance as measured in the Broadband Evaluation Board:  
CW,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 88\text{ mA}$ ,  $T_C = 25^\circ\text{C}$  (unless noted)

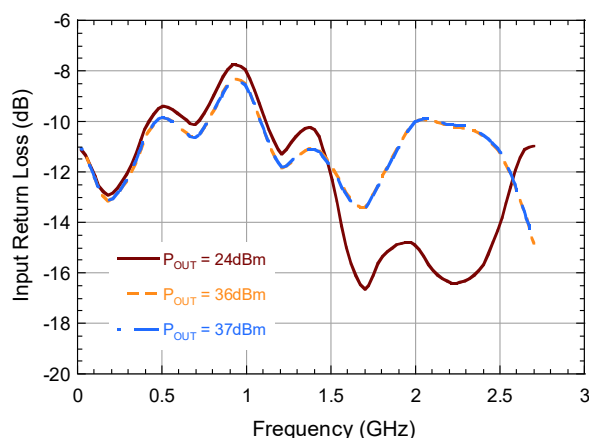
Gain vs. Frequency



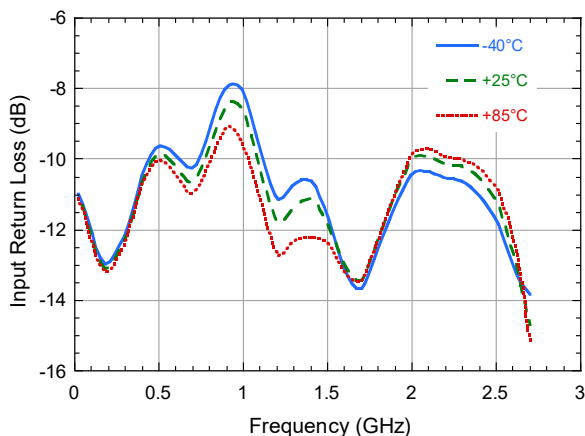
Gain vs. Frequency at  $P_{OUT} = 37\text{ dBm}$



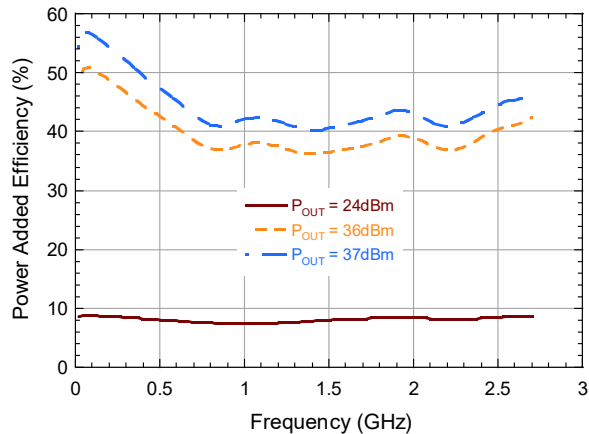
Input Return Loss vs. Frequency



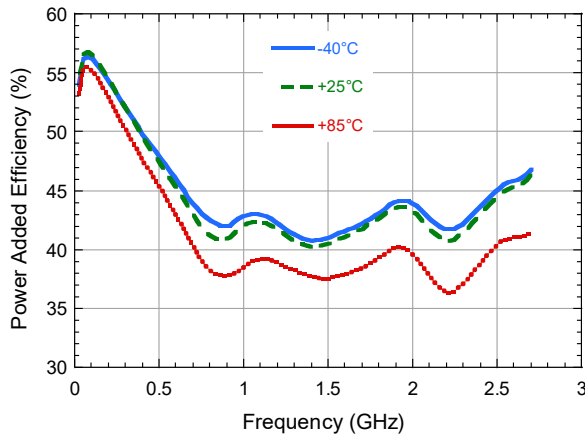
Input Return Loss at  $P_{OUT} = 37\text{ dBm}$  vs. Frequency



Power Added Efficiency vs. Frequency

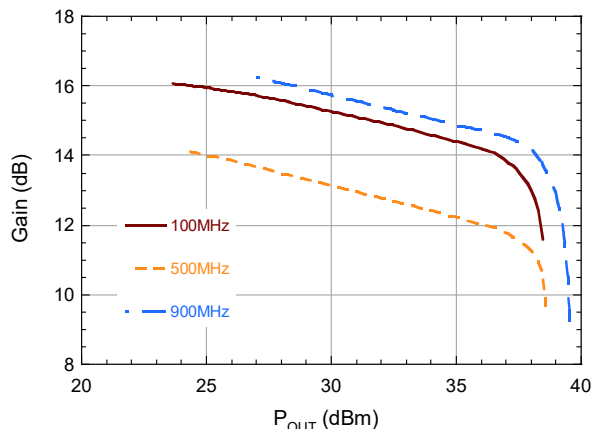


Power Added Efficiency at  $P_{OUT} = 37\text{ dBm}$  vs. Frequency

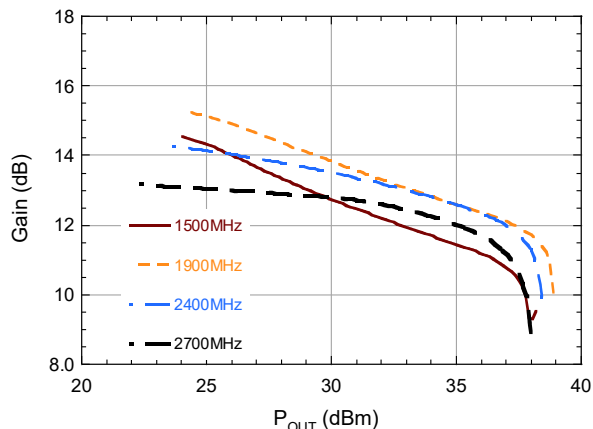


Typical Performance as measured in the Broadband Evaluation Board:  
CW,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 88\text{ mA}$ ,  $T_C = 25^\circ\text{C}$  (unless noted)

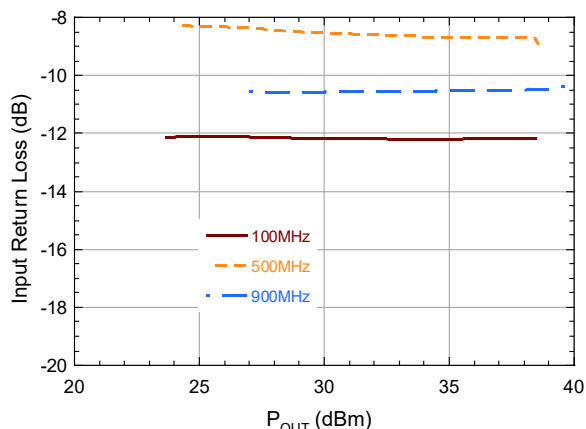
Gain vs.  $P_{OUT}$



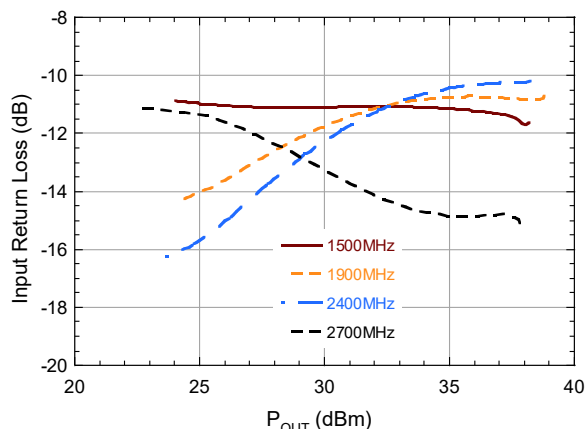
Gain vs.  $P_{OUT}$



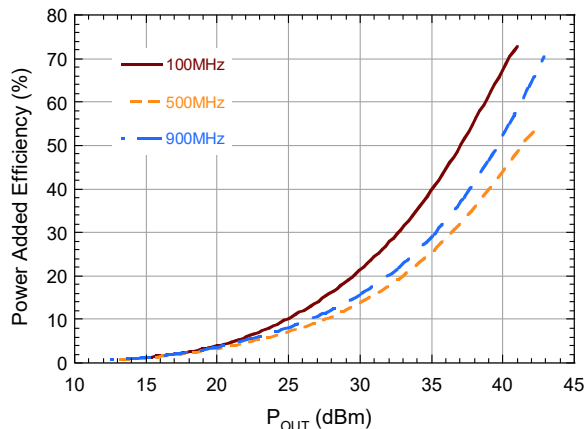
Input Return Loss vs.  $P_{OUT}$



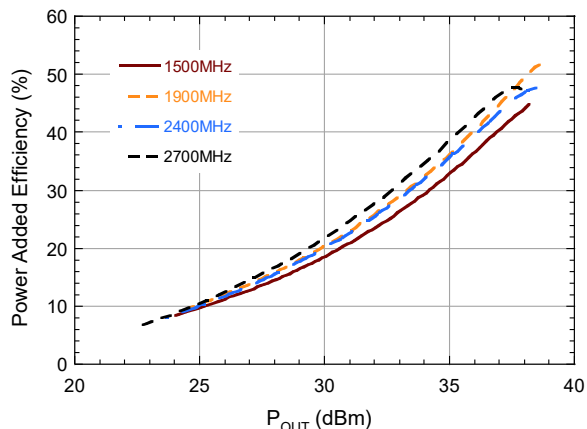
Input Return Loss vs.  $P_{OUT}$



Power Added Efficiency vs.  $P_{OUT}$



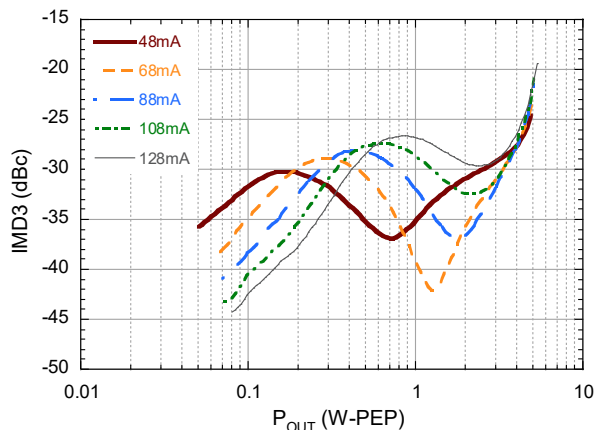
Power Added Efficiency vs.  $P_{OUT}$



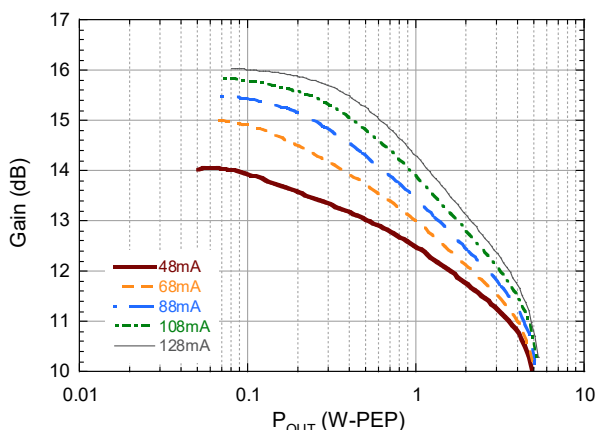


**Typical 2-Tone Performance as measured in the Broadband Evaluation Board  
1 MHz Tone Spacing, Freq = 1900 MHz,  $V_{DS} = 28$  V,  $I_{DQ} = 88$  mA,  $T_C = 25^\circ\text{C}$  (unless noted)**

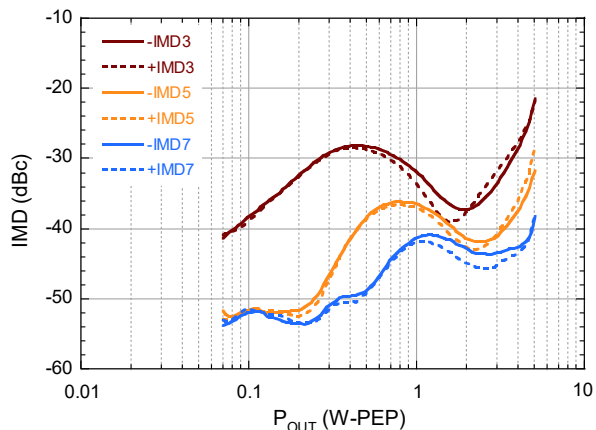
**2-Tone IMD vs. Output Power vs.  $I_{DQ}$**



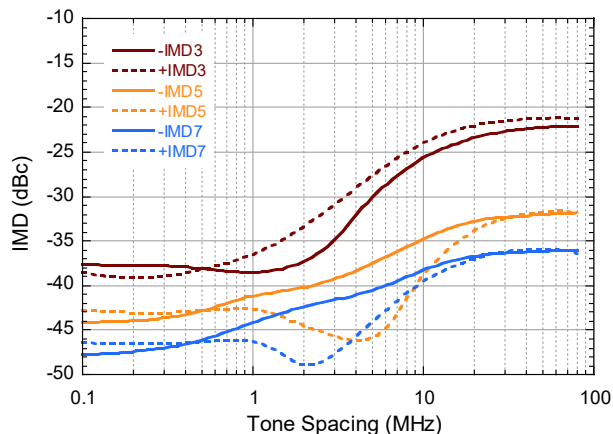
**2-Tone Gain vs. Output Power vs.  $I_{DQ}$**



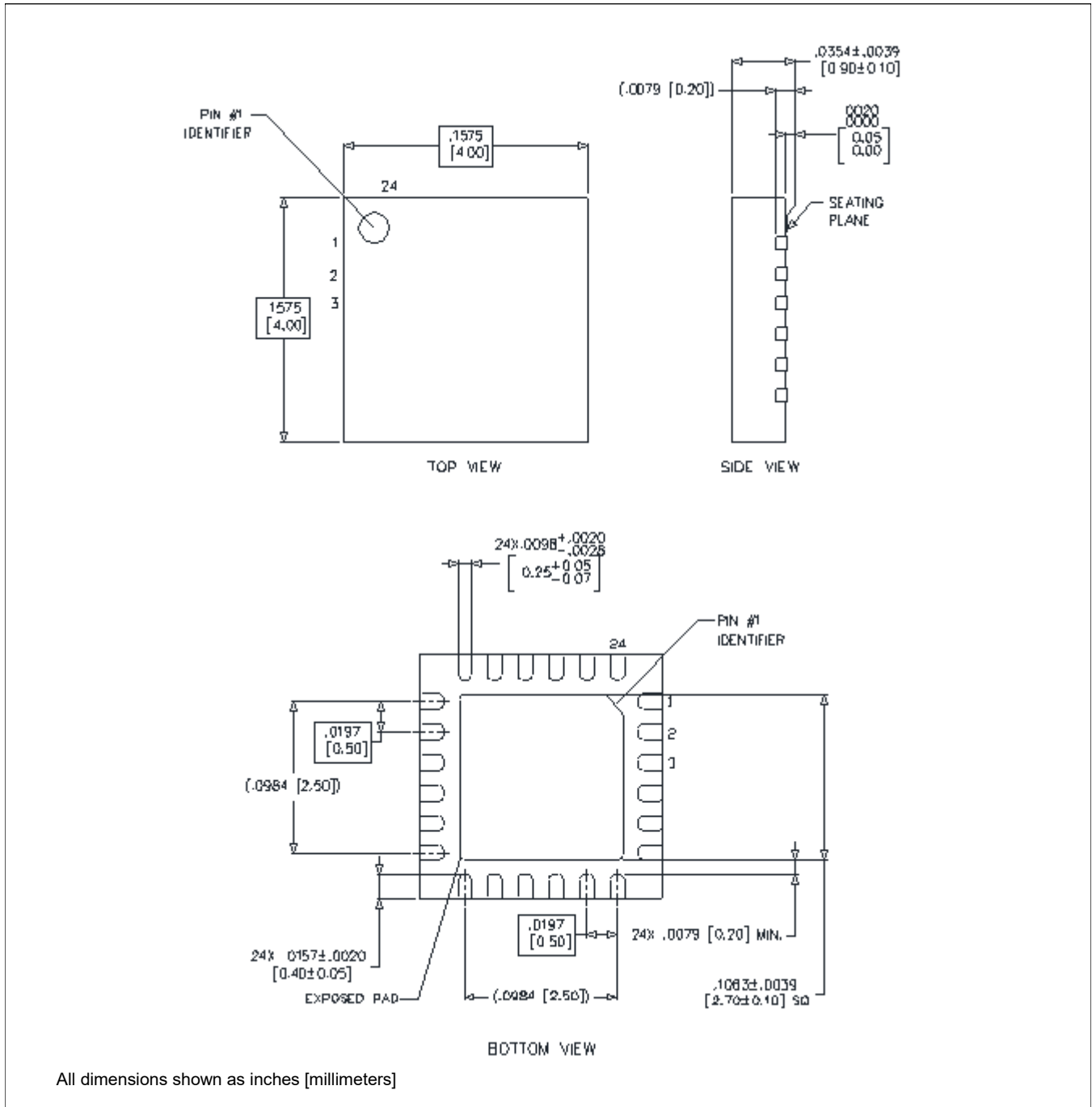
**2-Tone IMD vs. Output Power**



**2-Tone IMD vs. Tone Spacing ( $P_{OUT} = 37$  dBm-PEP)**



Lead-Free 4 mm 24-Lead QFN Plastic Package<sup>†</sup>



<sup>†</sup> Reference Application Note S2083 for lead-free solder reflow recommendations. Meets JEDEC moisture sensitivity level 3 requirements. Plating is Matte Tin.

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